

# Takeharu Kuroiwa

## List of Publications by Year in descending order

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papers

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docs citations

30  
times ranked

358  
citing authors

| #  | ARTICLE  | IF  | CITATIONS |
|----|--|-----|-----------|
| 1  | Practical applications of SiC-MOSFETs and further developments. Semiconductor Science and Technology, 2016, 31, 034003.  | 2.0 | 30        |
| 2  | Influence of Growth Pressure and Addition of HCl Gas on Growth Rate of 4H-SiC Epitaxy. Materials Science Forum, 2015, 821-823, 133-136.  | 0.3 | 4         |
| 3  | Evaluation of distribution of exchange coupling in CoFe/Ru/CoFe synthetic antiferromagnetic structure after annealing. Journal of Applied Physics, 2009, 105, .  | 2.5 | 4         |
| 4  | Suppression of Switching-Field Variation by Surface Oxidation Depending on the Shape of the CoFeB Free Layer. IEEE Transactions on Magnetics, 2007, 43, 2352-2354.   | 2.1 | 5         |
| 5  | Magnetization Chirality of Ni-Fe and Ni-Fe/Mn-Ir Asymmetric Ring Dots for High-Density Memory Cells. Materials Science Forum, 2006, 512, 171-176.  | 0.3 | 2         |
| 6  | Transition between onion states and vortex states in exchange-coupled Ni-Fe-Mn-Ir asymmetric ring dots. Journal of Applied Physics, 2006, 99, 08G303.  | 2.5 | 3         |
| 7  | Leakage current characteristics of Pt-Bi <sub>4-x</sub> La <sub>x</sub> Ti <sub>3</sub> O <sub>12</sub> -Ru ferroelectric capacitors fabricated on metal-organic chemical vapor deposited Ru films. Journal of Applied Physics, 2006, 100, 014108. | 2.5 | 1         |
| 8  | Thermal robustness in synthetic antiferromagnetic free layer for magnetic random access memory applications. Journal of Applied Physics, 2006, 99, 08C911.   | 2.5 | 3         |
| 9  | Magnetically pinned ring dots for spin valve or magnetic tunnel junction memory cells. Journal of Magnetism and Magnetic Materials, 2005, 286, 31-36.  | 2.3 | 21        |
| 10 | High-temperature operations of rotation angle sensors with spin-valve-type magnetic tunnel junctions. IEEE Transactions on Magnetics, 2005, 41, 3628-3630.   | 2.1 | 1         |
| 11 | Fatigueless Ferroelectric Capacitors with Ruthenium Bottom and Top Electrodes Formed by Metalorganic Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2005, 44, L378-L380.  | 1.5 | 4         |
| 12 | Control of pinned layer magnetization direction in spin-valve-type magnetic tunnel junction with an IrMn layer. Journal of Applied Physics, 2004, 95, 6795-6797.   | 2.5 | 1         |
| 13 | Read-Cycle Endurance of Magnetic Random Access Memory Elements. IEEE Transactions on Magnetics, 2004, 40, 2631-2633.   | 2.1 | 0         |
| 14 | Magnetization chirality due to asymmetrical structure in Ni-Fe annular dots for high-density memory cells. Journal of Applied Physics, 2004, 95, 6714-6716.  | 2.5 | 35        |
| 15 | Chemical Vapor Deposition of Ru Bottom Electrode for Ferroelectric Bi <sub>4-x</sub> La <sub>x</sub> Ti <sub>3</sub> O <sub>12</sub> Capacitors. Integrated Ferroelectrics, 2003, 59, 1437-1443.   | 0.7 | 0         |
| 16 | Chemical Vapor Deposition of Ru Bottom Electrode for Ferroelectric Bi <sub>4-x</sub> La <sub>x</sub> Ti <sub>3</sub> O <sub>12</sub> Capacitors. Integrated Ferroelectrics, 2003, 59, 1437-1443.   | 0.7 | 2         |
| 17 | Preparation of Bi <sub>3.25+x</sub> La <sub>0.75</sub> Ti <sub>3</sub> O <sub>12+y</sub> Films on Ruthenium Electrodes. Japanese Journal of Applied Physics, 2002, 41, 2105-2109.  | 1.5 | 14        |
| 18 | Improved fabrication process for Ru/BST/Ru capacitor by liquid source chemical vapor deposition. Thin Solid Films, 2002, 409, 8-14.  | 1.8 | 9         |

| #  | ARTICLE  | IF  | CITATIONS |
|----|--|-----|-----------|
| 19 | Effects of Oxygen Vacancy Diffusion on Leakage Characteristics of Pt/(Ba <sub>0.5</sub> Sr <sub>0.5</sub> )TiO <sub>3</sub> /Pt Capacitor. Japanese Journal of Applied Physics, 2000, 39, L416-L419.                       | 1.5 | 12        |
| 20 | Model of leakage characteristics of (Ba, $\hat{\text{e}}\%$ Sr)TiO <sub>3</sub> thin films. Applied Physics Letters, 1998, 73, 954-956.  | 3.3 | 82        |
| 21 | Influence of Buffer Layers and Barrier Metals on Properties of (Ba,Sr)TiO <sub>3</sub> Films Prepared by Liquid Source Chemical Vapor Deposition. Japanese Journal of Applied Physics, 1997, 36, 5874-5878.                | 1.5 | 10        |
| 22 | Novel stacked capacitor technology for 1-Gbit DRAMs with (Ba,Sr)TiO <sub>3</sub> thin films. Electronics and Communications in Japan, 1997, 80, 70-78.   | 0.2 | 2         |
| 23 | Determination of Structure Factors of Al<math>\text{O}_2\text{O}_3</math> by means of Large Angle Convergent Beam Electron Diffraction. Materials Transactions, JIM, 1995, 36, 1344-1348.                                  | 0.9 | 2         |
| 24 | Dielectric Relaxation of (Ba,Sr)TiO <sub>3</sub> Thin Films. Japanese Journal of Applied Physics, 1995, 34, 5478-5482.   | 1.5 | 87        |
| 25 | Dielectric Properties of (Ba <sub>x</sub> Sr <sub>1-x</sub> )TiO <sub>3</sub> Thin Films Prepared by RF Sputtering for Dynamic Random Access Memory Application. Japanese Journal of Applied Physics, 1994, 33, 5187-5191. | 1.5 | 110       |
| 26 | Electric Properties of SrTiO <sub>3</sub> Thin Films Prepared by RF Sputtering. Japanese Journal of Applied Physics, 1992, 31, 3025-3028.  | 1.5 | 52        |
| 27 | Characteristics of a Schottky Barrier Diode and the SiC Wafers Sliced by Wire Electrical Discharge Machining. Materials Science Forum, 0, 778-780, 784-787.  | 0.3 | 0         |
| 28 | Demonstration of High Quality 4H-SiC Epitaxy by Using the Two-Step Growth Method. Materials Science Forum, 0, 778-780, 167-170.  | 0.3 | 4         |
| 29 | Demonstration of High Quality 4H-SiC Epitaxial Growth with Extremely Low Basal Plane Dislocation Density. Materials Science Forum, 0, 778-780, 91-94.  | 0.3 | 9         |
| 30 | Properties of a SiC Schottky Barrier Diode Fabricated with a Thin Substrate. Materials Science Forum, 0, 778-780, 820-823.   | 0.3 | 7         |